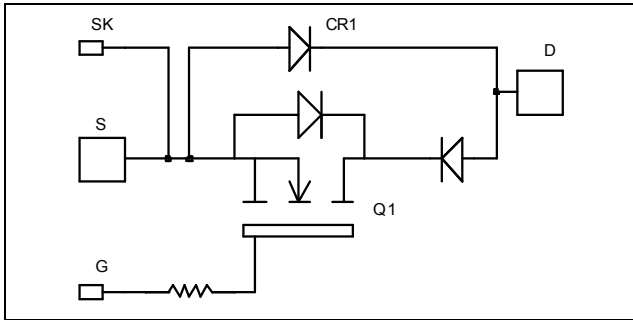


*Single switch
Series & parallel diodes
MOSFET Power Module*

**$V_{DSS} = 500V$
 $R_{DSon} = 19m\Omega$ max @ $T_j = 25^\circ C$
 $I_D = 163A$ @ $T_c = 25^\circ C$**



Application

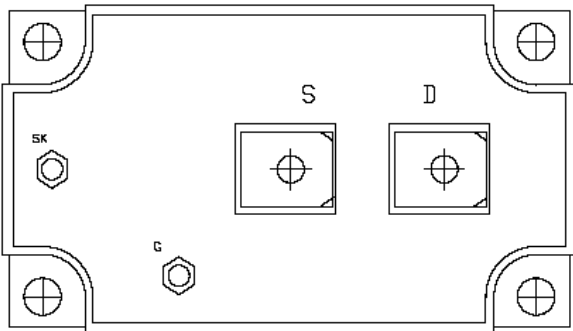
- Motor control
- Switched Mode Power Supplies
- Uninterruptible Power Supplies

Features

- Power MOS 7[®] MOSFETs
 - Low R_{DSon}
 - Low input and Miller capacitance
 - Low gate charge
 - Avalanche energy rated
 - Very rugged
- Kelvin source for easy drive
- Low stray inductance
 - M6 power connectors
 - M4 signal connectors
- High level of integration

Benefits

- Outstanding performance at high frequency operation
- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance



Absolute maximum ratings

Symbol	Parameter	Max ratings	Unit
V_{DSS}	Drain - Source Breakdown Voltage	500	V
I_D	Continuous Drain Current	$T_c = 25^\circ C$	163
		$T_c = 80^\circ C$	122
I_{DM}	Pulsed Drain current	652	A
V_{GS}	Gate - Source Voltage	± 30	V
R_{DSon}	Drain - Source ON Resistance	19	$m\Omega$
P_D	Maximum Power Dissipation	$T_c = 25^\circ C$	1136
I_{AR}	Avalanche current (repetitive and non repetitive)	46	A
E_{AR}	Repetitive Avalanche Energy	50	mJ
E_{AS}	Single Pulse Avalanche Energy	2500	

CAUTION: These Devices are sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed.

All ratings @ $T_j = 25^\circ\text{C}$ unless otherwise specified

Electrical Characteristics

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
BV_{DSS}	Drain - Source Breakdown Voltage	$V_{GS} = 0V, I_D = 500\mu A$	500			V
I_{DSS}	Zero Gate Voltage Drain Current	$V_{GS} = 0V, V_{DS} = 500V$ $T_j = 25^\circ\text{C}$			200	μA
		$V_{GS} = 0V, V_{DS} = 400V$ $T_j = 125^\circ\text{C}$			1000	
$R_{DS(on)}$	Drain - Source on Resistance	$V_{GS} = 10V, I_D = 81.5A$			19	$m\Omega$
$V_{GS(th)}$	Gate Threshold Voltage	$V_{GS} = V_{DS}, I_D = 10mA$	3		5	V
I_{GSS}	Gate - Source Leakage Current	$V_{GS} = \pm 30V, V_{DS} = 0V$			± 200	nA

Dynamic Characteristics

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
C_{iss}	Input Capacitance	$V_{GS} = 0V$ $V_{DS} = 25V$ $f = 1MHz$		22.4		nF
C_{oss}	Output Capacitance			4.8		
C_{rss}	Reverse Transfer Capacitance			0.36		
Q_g	Total gate Charge	$V_{GS} = 10V$ $V_{Bus} = 250V$ $I_D = 163A$		492		nC
Q_{gs}	Gate - Source Charge			132		
Q_{gd}	Gate - Drain Charge			260		
$T_{d(on)}$	Turn-on Delay Time	Inductive switching @ 125°C $V_{GS} = 15V$ $V_{Bus} = 333V$ $I_D = 163A$ $R_G = 1\Omega$		18		ns
T_r	Rise Time			35		
$T_{d(off)}$	Turn-off Delay Time			87		
T_f	Fall Time			77		
E_{on}	Turn-on Switching Energy ❶	Inductive switching @ 25°C $V_{GS} = 15V, V_{Bus} = 333V$ $I_D = 163A, R_G = 1\Omega$		3020		μJ
E_{off}	Turn-off Switching Energy ❷			2904		
E_{on}	Turn-on Switching Energy ❶	Inductive switching @ 125°C $V_{GS} = 15V, V_{Bus} = 333V$ $I_D = 163A, R_G = 1\Omega$		4964		μJ
E_{off}	Turn-off Switching Energy ❷			3384		

❶ E_{on} includes diode reverse recovery.

❷ In accordance with JEDEC standard JESD24-1.

Series diode ratings and characteristics

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
$I_{F(AV)}$	Maximum Average Forward Current	50% duty cycle $T_c = 85^\circ\text{C}$		120		A
V_F	Diode Forward Voltage	$I_F = 120A$		1.1	1.15	V
		$I_F = 240A$		1.4		
		$I_F = 120A$ $T_j = 125^\circ\text{C}$		0.9		
t_{rr}	Reverse Recovery Time	$I_F = 120A$ $V_R = 133V$ $di/dt = 400A/\mu s$ $T_j = 25^\circ\text{C}$		31		ns
		$T_j = 125^\circ\text{C}$		60		
Q_{rr}	Reverse Recovery Charge	$I_F = 120A$ $V_R = 133V$ $di/dt = 400A/\mu s$ $T_j = 25^\circ\text{C}$		120		nC
		$T_j = 125^\circ\text{C}$		500		

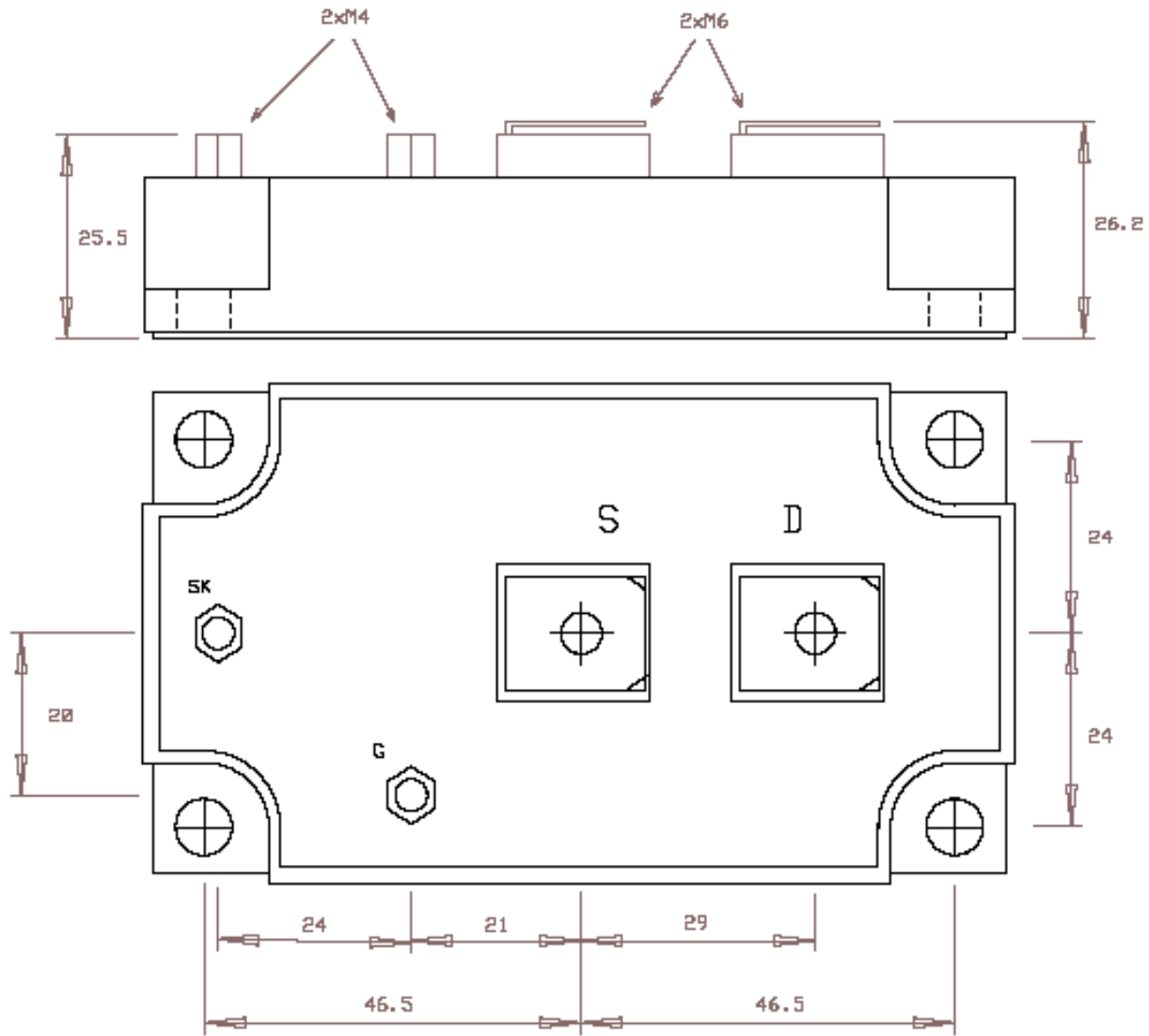
Parallel diode ratings and characteristics

<i>Symbol</i>	<i>Characteristic</i>	<i>Test Conditions</i>		<i>Min</i>	<i>Typ</i>	<i>Max</i>	<i>Unit</i>
$I_{F(AV)}$	Maximum Average Forward Current	50% duty cycle	$T_c = 80^\circ\text{C}$		100		A
V_F	Diode Forward Voltage	$I_F = 100\text{A}$			1.6	1.8	V
		$I_F = 200\text{A}$			1.9		
		$I_F = 100\text{A}$	$T_j = 125^\circ\text{C}$		1.4		
t_{rr}	Reverse Recovery Time	$I_F = 100\text{A}$ $V_R = 400\text{V}$ $di/dt = 200\text{A}/\mu\text{s}$	$T_j = 25^\circ\text{C}$		180		ns
			$T_j = 125^\circ\text{C}$		220		
Q_{rr}	Reverse Recovery Charge	$I_F = 100\text{A}$ $V_R = 400\text{V}$ $di/dt = 200\text{A}/\mu\text{s}$	$T_j = 25^\circ\text{C}$		390		nC
			$T_j = 125^\circ\text{C}$		1450		

Thermal and package characteristics

<i>Symbol</i>	<i>Characteristic</i>		<i>Min</i>	<i>Typ</i>	<i>Max</i>	<i>Unit</i>
R_{thJC}	Junction to Case	Transistor			0.11	$^\circ\text{C}/\text{W}$
		Series diode			0.46	
		Parallel diode			0.6	
V_{ISOL}	RMS Isolation Voltage, any terminal to case $t = 1\text{ min}$, $I_{isol} < 1\text{mA}$, 50/60Hz		2500			V
T_J	Operating junction temperature range		-40		150	$^\circ\text{C}$
T_{STG}	Storage Temperature Range		-40		125	
T_C	Operating Case Temperature		-40		100	
Torque	Mounting torque	M4			1.2	
		M6	3		5	
Wt	Package Weight				400	g

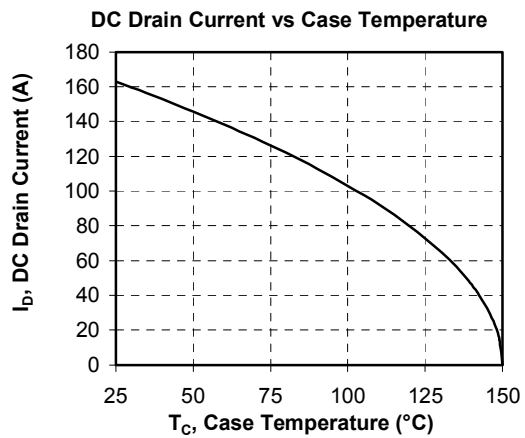
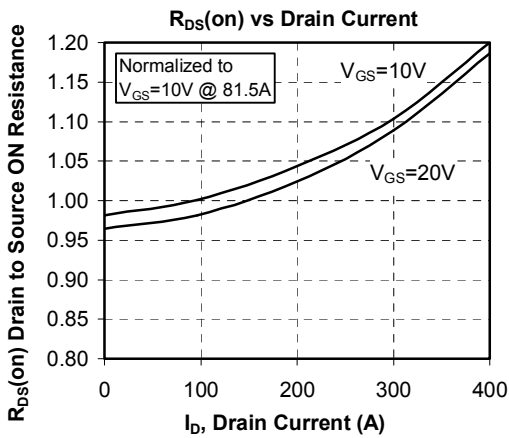
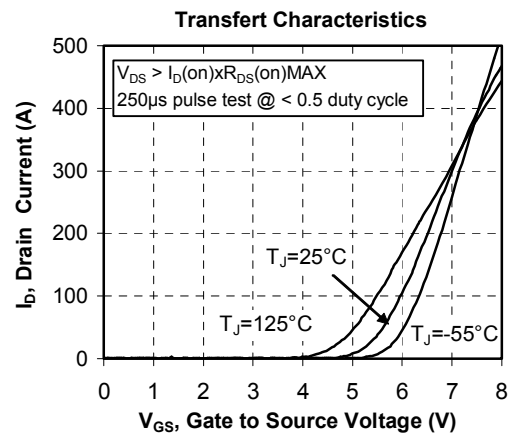
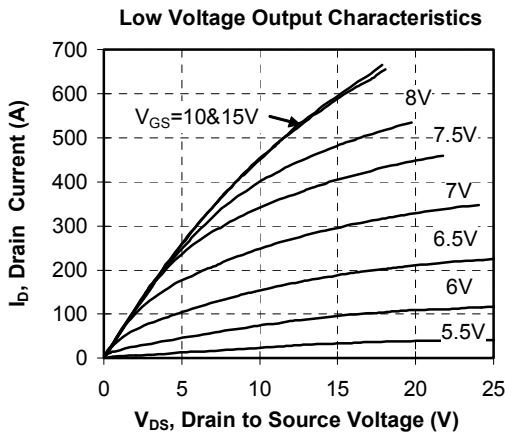
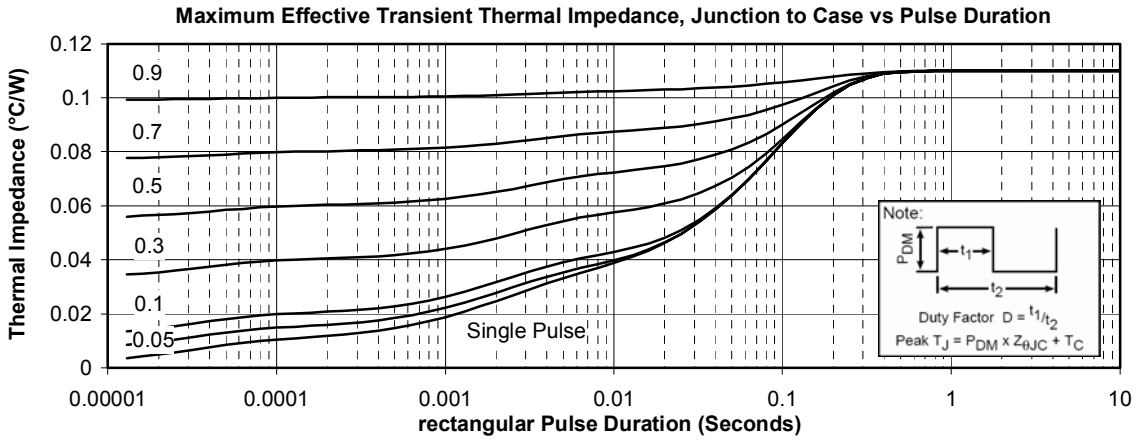
Package outline

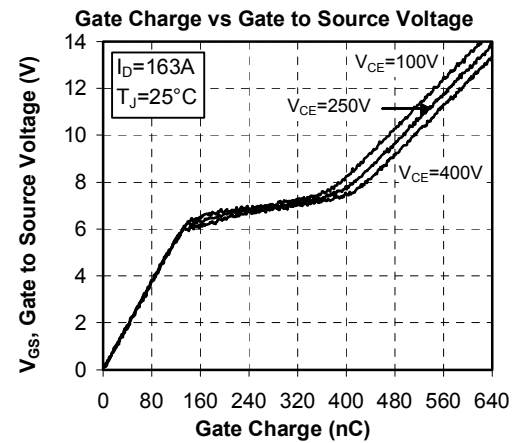
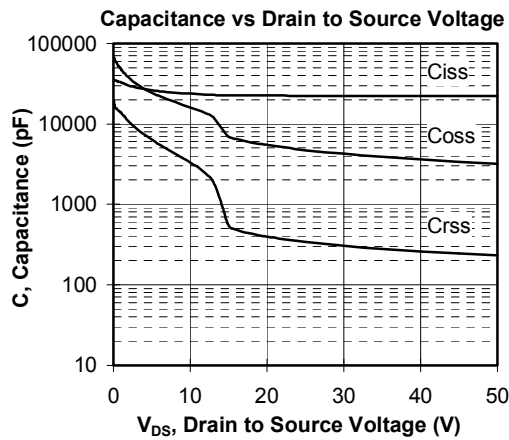
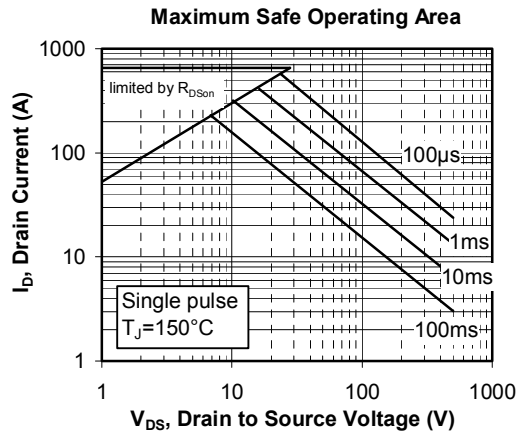
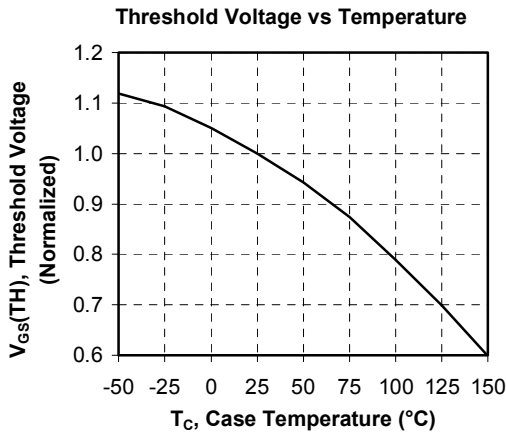
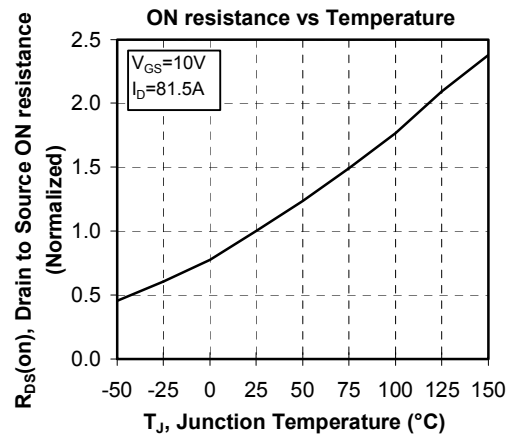
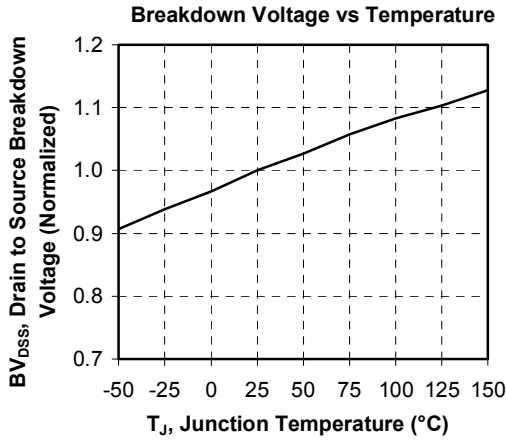


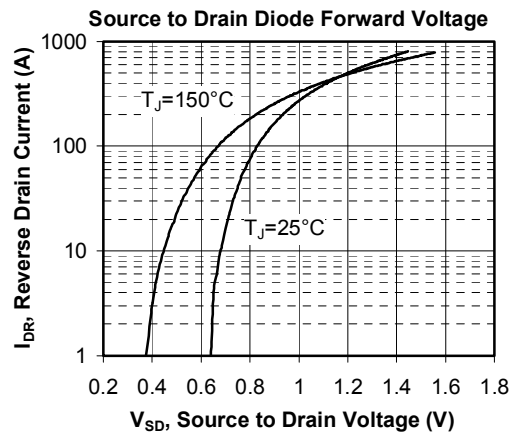
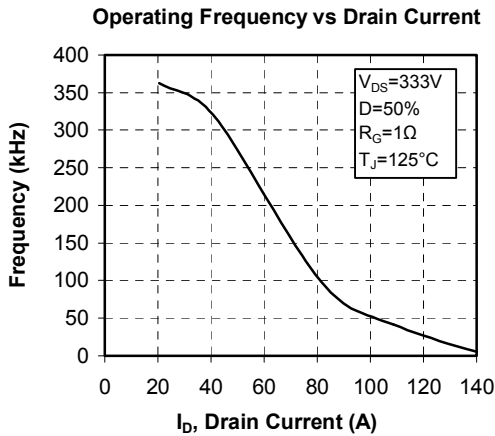
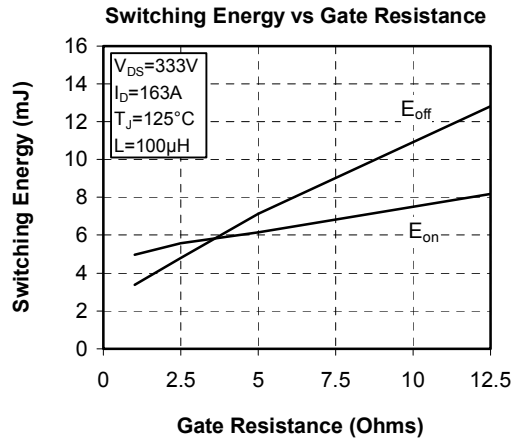
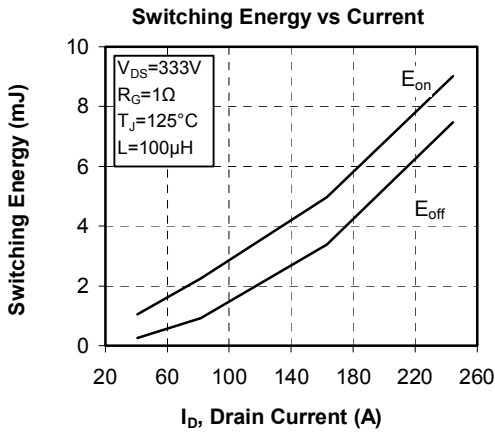
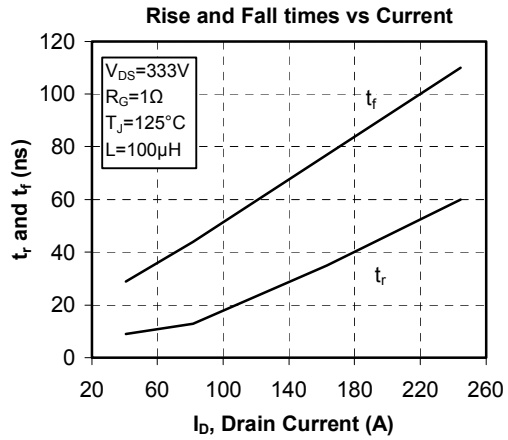
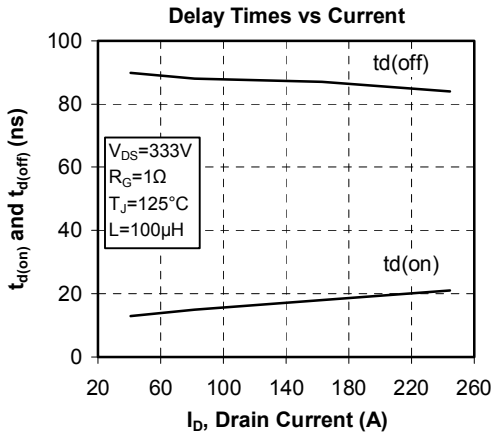
GENERAL TOLERANCES : +/-0.5mm

Mounting holes: 4xØ6.5 mm

Typical Performance Curve







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APT's products are covered by one or more of U.S. patents 4,895,810 5,045,903 5,089,434 5,182,234 5,019,522 5,262,336 6,503,786 5,256,583 4,748,103 5,283,202 5,231,474 5,434,095 5,528,058 and foreign patents. U.S. and Foreign patents pending. All Rights Reserved.